



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



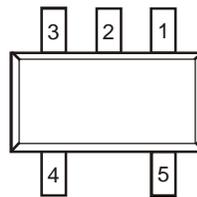
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## Features

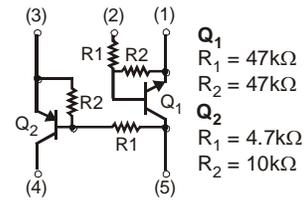
- Ultra-Small Surface Mount Package
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space

## Mechanical Data

- Case: SOT353
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208  $\text{Q3}$
- Weight: 0.006 grams (Approximate)



Package Pin Out Configuration



Device Schematic

**Absolute Maximum Ratings, Pre-Biased NPN Transistor, Q<sub>1</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	50	V
Input Voltage	V <sub>IN</sub>	-10 to +40	V
Output Current	I <sub>O</sub>	30	mA
Collector Current	I <sub>C(MAX)</sub>	100	mA

**Absolute Maximum Ratings, Pre-Biased PNP Transistor, Q<sub>2</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	-50	V
Input Voltage	V <sub>IN</sub>	-20 to +7	V
Output Current	I <sub>O</sub>	-100	mA
Collector Current	I <sub>C(MAX)</sub>	-100	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	290	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>θJA</sub>	430	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics, Pre-Biased NPN Transistor, Q<sub>1</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Input Voltage	(Note 7)	V <sub>I(OFF)</sub>	0.5	—	—	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA
	(Note 8)	V <sub>I(ON)</sub>	—	—	3	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 2mA
Output Voltage	V <sub>O(ON)</sub>	—	0.1	0.3	V	I <sub>O</sub> /I <sub>I</sub> = 10mA/0.5 mA	
Input Current	I <sub>I</sub>	—	—	0.18	mA	V <sub>I</sub> = 5V	
Output Current	I <sub>O(OFF)</sub>	—	—	0.5	μA	V <sub>CC</sub> = 50V, V <sub>I</sub> = 0V	
DC Current Gain	G <sub>I</sub>	68	—	—	—	V <sub>O</sub> = 5V, I <sub>O</sub> = 5mA	
Gain-Bandwidth Product (Note 9)	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz	
Input Resistance	R <sub>1</sub>	32.9	47	61.1	kΩ	—	
Resistance Ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	—	—	

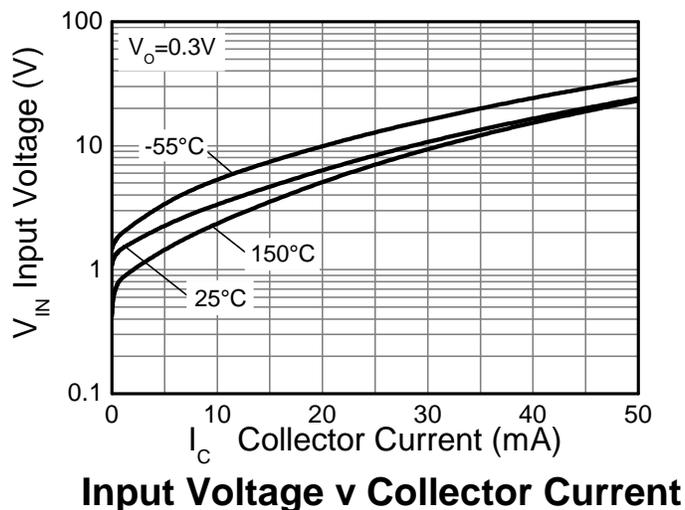
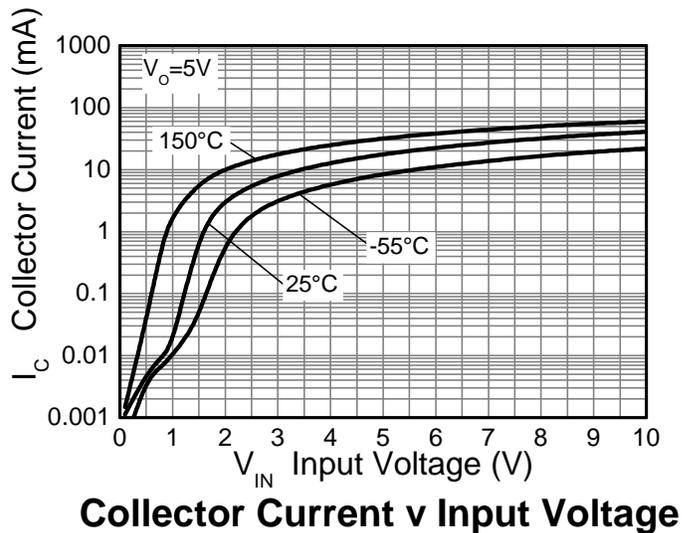
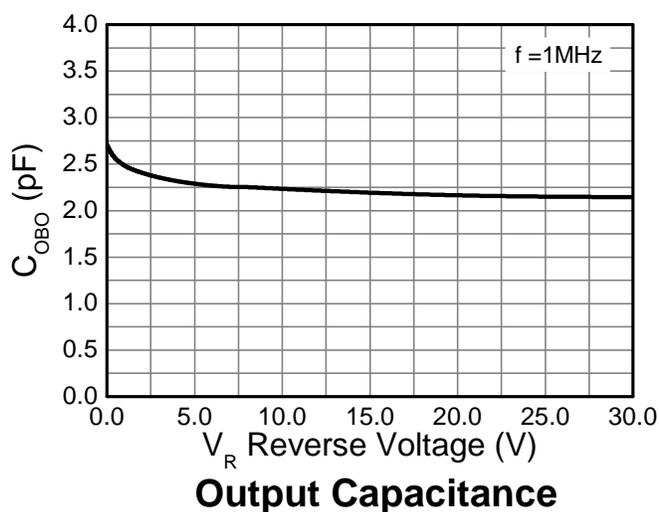
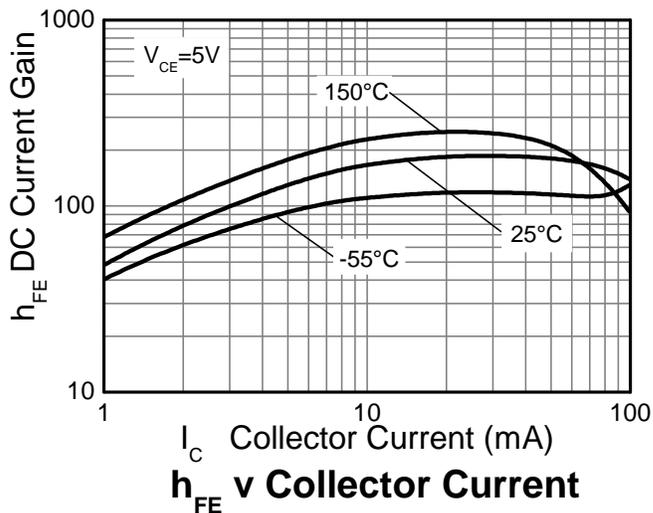
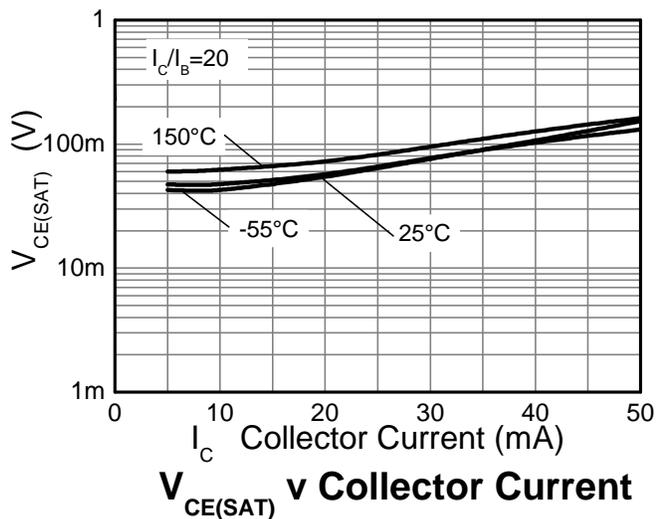
- Notes:
- The device is guaranteed to be in "OFF" state with V<sub>I(OFF)</sub> up to 0.5V.
  - The device is guaranteed to be in "ON" state with V<sub>I(ON)</sub> starting from 3V.
  - Characteristic of Transistor – for reference only.

**Electrical Characteristics, Pre-Biased PNP Transistor, Q<sub>2</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

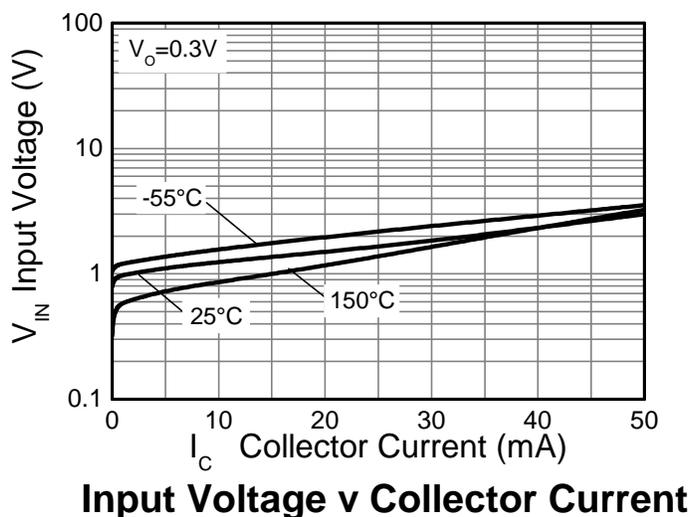
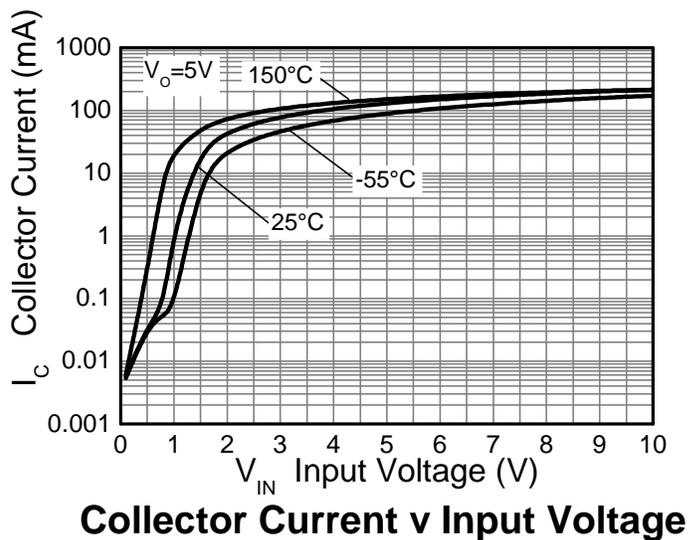
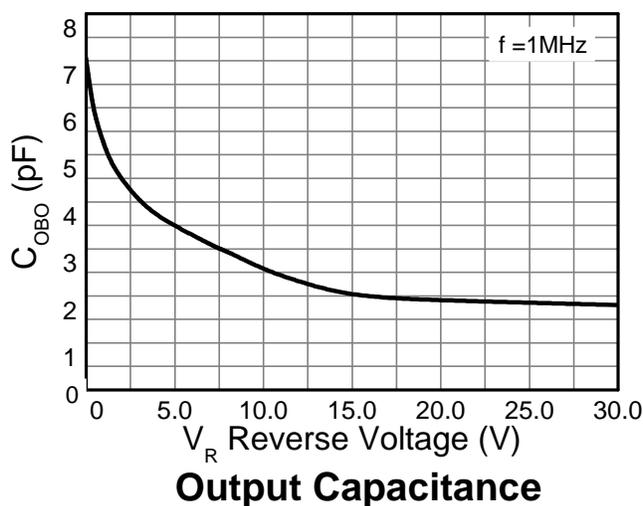
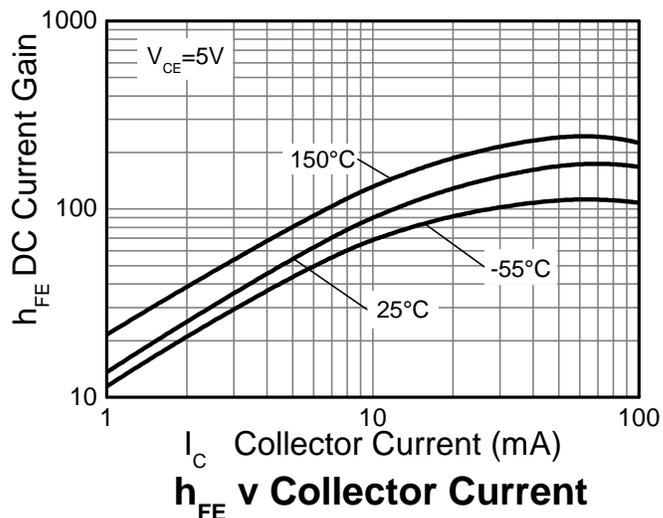
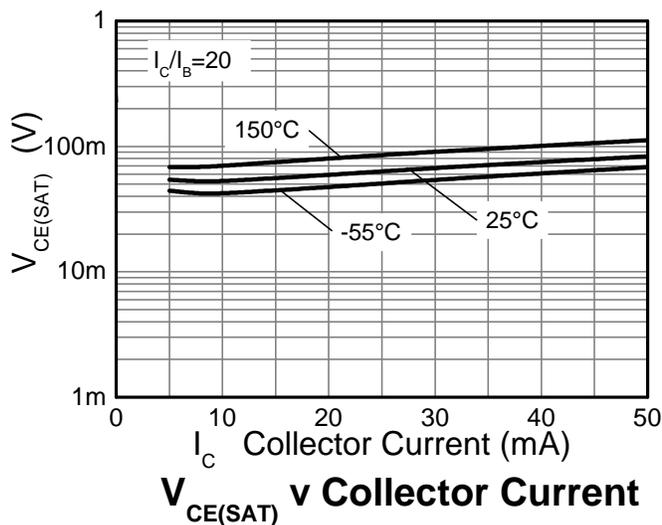
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Input Voltage	(Note 10)	V <sub>I(OFF)</sub>	-0.3	—	—	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	(Note 11)	V <sub>I(ON)</sub>	—	—	-2.5	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA
Output Voltage	V <sub>O(ON)</sub>	—	-0.1	-0.3	V	I <sub>O</sub> /I <sub>I</sub> = -10mA/-0.5 mA	
Input Current	I <sub>I</sub>	—	—	-1.8	mA	V <sub>I</sub> = -5V	
Output Current	I <sub>O(OFF)</sub>	—	—	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V	
DC Current Gain	G <sub>I</sub>	30	—	—	—	V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA	
Gain-Bandwidth Product (Note 9)	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz	
Input Resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	—	
Resistance Ratio	R <sub>2</sub> /R <sub>1</sub>	1.7	2.1	2.6	—	—	

- Notes:
- The device is guaranteed to be in "OFF" state with V<sub>I(OFF)</sub> up to -0.3V.
  - The device is guaranteed to be in "ON" state with V<sub>I(ON)</sub> starting from -2.5V.

**Typical Electrical Characteristics – NPN Section** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

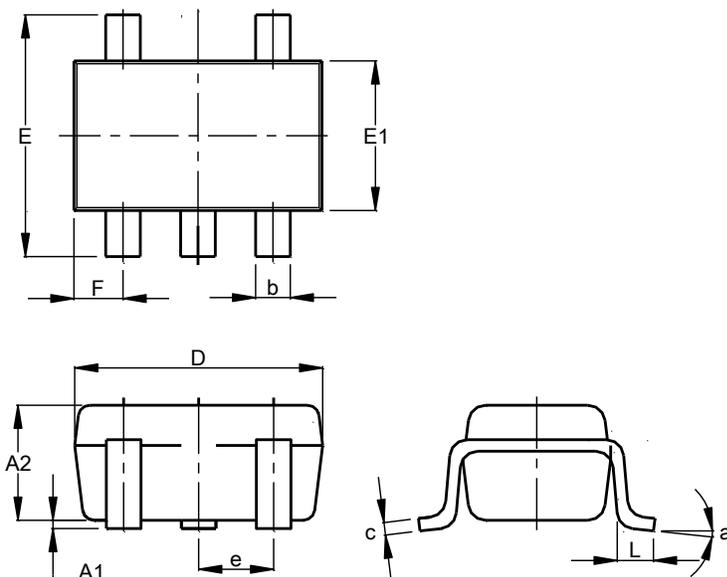


**Typical Electrical Characteristics – PNP Section** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



## Package Outline Dimensions

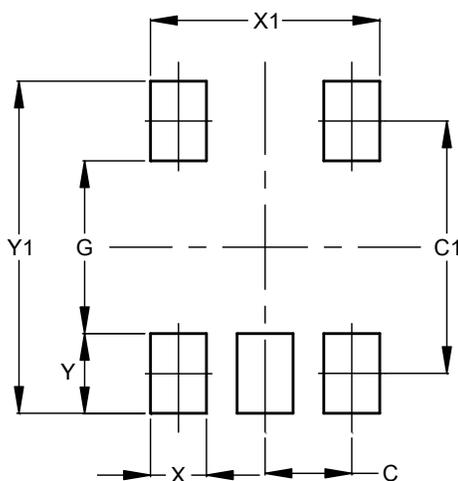
SOT353



SOT353			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT353



Dimensions	Value (in mm)
C	0.650
C1	1.900
G	1.300
X	0.420
X1	1.720
Y	0.600
Y1	2.500